





### **Features**

- Reflow Process Compatible
- AT-Cut and SC-Cut Crystal Options
- Low Profile Compact Package

## **Applications**

- · Base Stations
- Test Equipment
- Synthesizers
- Military Communication Equipment
- Digital Switching

## **Performance Specifications**

Frequency Stabilities <sup>1</sup> (AT-Cut Crystal-Standard)						
Parameter	Min	Typical	Max	Unit	Condition	
vs. operating temperature range (referenced to +25°C)	-50 -100 -150 -200		+50 +100 +150 +200	ppb ppb ppb ppb	0 to +70°C -20 to +70°C -40 to +70°C -40 to +85°C	
Initial tolerance vs. supply voltage change vs. load change vs. aging/day vs. aging/1st year vs. aging/year (following years)	-0.3 -10 -10 -2 -500 -250		+0.3 +10 +10 +2 +500 +250	ppm ppb ppb ppb ppb ppb	at time of shipment, nominal EFC $V_s \pm 5\%$ static Load $\pm 5\%$ static after 30 days of operation after 30 days of operation after 30 days of operation	
Warm-up time			5	minutes	to ±100ppb of final frequency (1 hour reading) @ +25°C	
	Frequer	ıcy Stabilit	ies¹ (SC-Cu	t Crystal-Opt	ion)	
vs. operating temperature range (referenced to +25°C)	-10 -20 -25 -30		+10 +20 +25 +30	ppb ppb ppb ppb	0 to +70°C -20 to +70°C -40 to +70°C -40 to +85°C	
Initial tolerance vs. supply voltage change vs. load change vs. aging/day vs. aging/1st year vs. aging/year (following years)	-100 -5 -5 -1 -100 -50		+100 +5 +5 +1 +100 +50	ppb ppb ppb ppb ppb	at time of shipment, nominal EFC $V_s \pm 5\%$ static Load $\pm 5\%$ static after 30 days of operation after 30 days of operation after 30 days of operation	
Warm-up time			5	minutes	to $\pm 10$ ppb of final frequency (1 hour reading) @ $+25^{\circ}$ C	

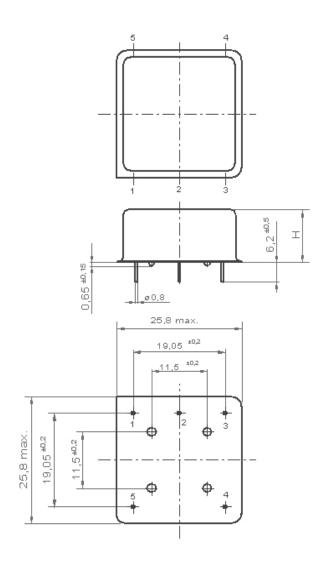
# **Performance Specifications**

Supply Voltage (Vs)						
Parameter	Min	Typical	Max	Unit	Condition	
Supply Voltage	3.135	3.3	3.465	VDC		
Supply Voltage	4.75	5.0	5.25	VDC		
Supply Voltage	11.4	12.0	12.6	VDC		
Power Consumption			3.0 1.0	Watts Watts		varm-up te @ +25°C
RF Output						
Signal [Standard]		HCI	MOS			
Load		15		pF		
Signal Level (Vol)			0.4 0.5	VDC VDC	with Vs=3.3V a with Vs=5V & 12V	nnd 15 pF Load V and 15 pF Load
Signal Level (Voh)	2.4 3.5			VDC VDC		nd 15 pF Load V and 15 pF Load
Duty Cycle	45		55	%	@ (Voh	n-Vol)/2
Signal		Sine	wave			
Load		50		Ohms		
Output Power	+2.0 +5.0	+5.0 +8.0	+8.0 +11.0	dBm dBm	with Vs=3.3V and 50 Ohm load with Vs=5V & 12V and 50 Ohm load	
Harmonics			-30	dBc	50 Ohm load	
		Freque	ncy Tuning	(EFC)		
Tuning Slope		Fixed OCX	); No adjust			
Tuning Range	±3.0 ±0.75		±8.0 ±2.0	ppm ppm	with AT cut crystal with SC cut crystal	
Linearity			10	%		
Tuning Slope		Pos	itive			
Control Voltage Range	0.0 0.0	1.4 2.0	2.8 4.0	VDC VDC	with Vs=3.3V with Vs=5V & 12V	
	R	eference V	oltage Out	put (VRef)		
Reference Voltage	2.75 3.92 4.9	2.8 4.0 5.0	2.85 4.08 5.1	VDC VDC VDC	with Vs=3.3V with Vs=5V with Vs=12V	
Additional Parameters						
Phase Noise <sup>3</sup>			-90 -120 -140 -145 -150	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	1 Hz 10 Hz 100 Hz 1 kHz 10 kHz	@ 10MHz with SC cut
Phase Noise <sup>3</sup>			-75 -100 -130 -140 -150	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	1 Hz 10 Hz 100 Hz 1 kHz 10 kHz	@ 10MHz with AT cut
Weight			14	g		

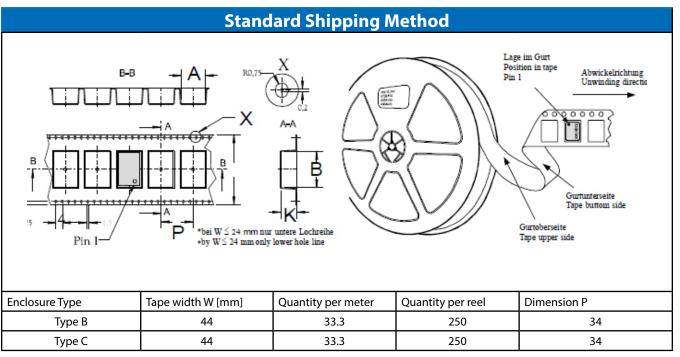
Absolute Maximum Ratings					
Parameter	Min	Typical	Max	Unit	Condition
Supply Voltage (Vs)			6.5 15	V V	with Vs=3.3V & 5V with Vs=12V
Output Load			50	рF	
Operable Temperature Range	-55		+85	°C	
Storage Temperature Range	-55		+125	°C	

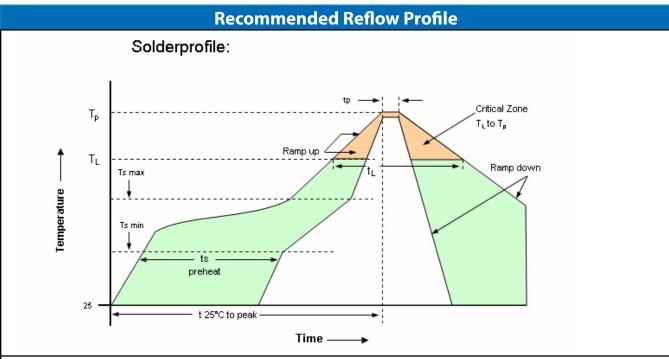
Environmental and Product Classification					
Shock (Endurance)	MIL-STD-202, Method 213, Condition J, 30 g 11 ms				
Sine Vibration (Endurance)	MIL-STD-202,	MIL-STD-202, Method 201 and 204, Condition A, except 5 g to 500 Hz, 1 sweep each axis			
Random Vibration (Endurance)	MIL-STD-202,	Method 214	, Condition I-	D	
Humidity	MIL-STD-202, Method 103, Condition B, 100% rh				
Seal	MIL-STD-202, Method 112, Condition D				
Altitude	MIL-STD-202, Method 105, sea level to30,000 ft				
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition A,B,C				
Terminal Strength	MIL-STD-202, Method 11, Condition C (5 bends at 45°, 2 lbs)				
Moisture Sensitive Level	1				
RoHS	6 (fully compliant) - no pure tin options available upon request, the device will be assigned a customer part number , not orderable through ordering codes				
Storage Temperature Range	-55 +125 °C				

# Outline Drawing / Enclosure



OX-200							
Code	Height "H"	Pin Length "L" Min					
0	10.4	6.2					
1	12.7	6.2					
2	13.4	6.2					
	Pin Connections						
1	RF Output						
2	Ground (Case)						
3	Electronic Frequency Control Input (EFC)						
4	Reference Voltage Option						
5	Supply Voltage Input (VS)						

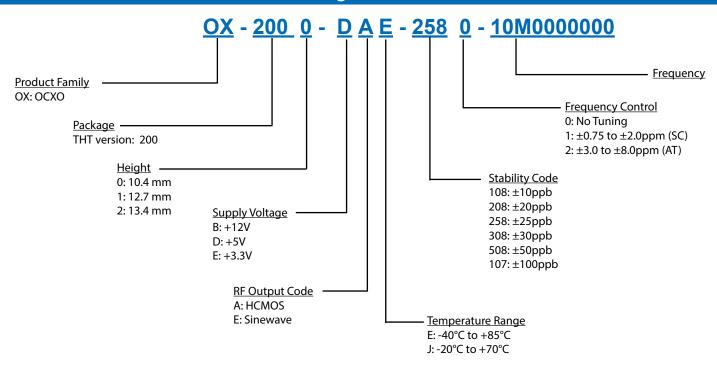




Profile Feature	Pb-Free Assembly /Sn-Pb Assembly	Profile Feature	Pb-Free Assembly /Sn-Pb Assembly
Average ramp-up rate (T <sub>L</sub> to Tp)	3°C/second max.	Time 25°C to Peak Temperature	8 minutes max.
Preheat -Temperature Min Ts <sub>min</sub> ) -Temperature Min Ts <sub>max</sub> ) -Time (min to max) (ts)	150°c 200°c 60-180 seconds	Time maintainted above - Temperature (T <sub>L</sub> ) - Time (t <sub>L</sub> )	217°C 60-150 seconds
Ts <sub>max</sub> to T <sub>L</sub> - Ramp-up Rate	3°C/second max.		
Time maintainted above - Temperature (T <sub>L</sub> ) - Time (t <sub>L</sub> )	217°C 60-150 seconds	Time within 5°C of actual Peak Temperature (tp)	20-40 seconds
Peak Temperature (Tp)	max 260°C	Ramp-down Rate	6°C/second max.

Note: All temperatures refer to topside of the package, measured on the package body surface.

### **Ordering Information**



#### Notes:

- Contact factory for improved stabilities or additional product options. Not all options and codes are available at all
- Unless other stated all values are valid after warm-up time and refer to typical conditions for supply voltage, frequency control voltage, load, temperature (25°C).
- Phase noise degrades with increasing output frequency.
- Subject to technical modification.
- Contact factory for availability.



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